Abstracts

X-Band MMIC Amplifier with Pulse-Doped GaAs MESFETs (1991 Vol. I [MWSYM])

N. Shiga, S. Nakajima, K. Otobe, T. Sekiguchi, N. Kuwata, K.-I. Matsuzaki and H. Hayashi. "X-Band MMIC Amplifier with Pulse-Doped GaAs MESFETs (1991 Vol. I [MWSYM])." 1991 MTT-S International Microwave Symposium Digest 91.1 (1991 Vol. I [MWSYM]): 77-80.

An X-band monolithic low noise amplifier (LNA) with 0.5µm-gate pulse-doped GaAs MESFETs was successfully demonstrated for a direct broadcast satellite (DBS) converter. This LNA shows excellent VSWR matches of under 1.4 as well as a noise figure of 1.67dB and a gain of 24dB at 12GHz. The yield of chips within microwave specifications is 62.5%.

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